

NCE N-Channel Enhancement Mode Power MOSFET

Description

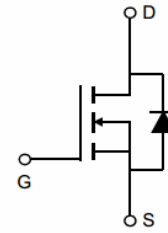
The NCE2004Y uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

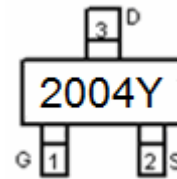
- $V_{DS} = 20V, I_D = 4A$
 $R_{DS(ON)} < 24m\Omega @ V_{GS} = 4.5V$
 $R_{DS(ON)} < 32m\Omega @ V_{GS} = 2.5V$
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current

Application

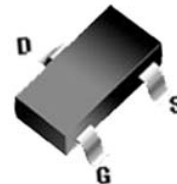
- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



Schematic diagram



Marking and pin Assignment



SOT-23-3L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
2004Y	NCE2004Y	SOT23-3L	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D	4	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D(100^\circ C)$	2.8	A
Pulsed Drain Current	I_{DM}	20	A
Maximum Power Dissipation	P_D	1.0	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	125	$^\circ C/W$
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Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

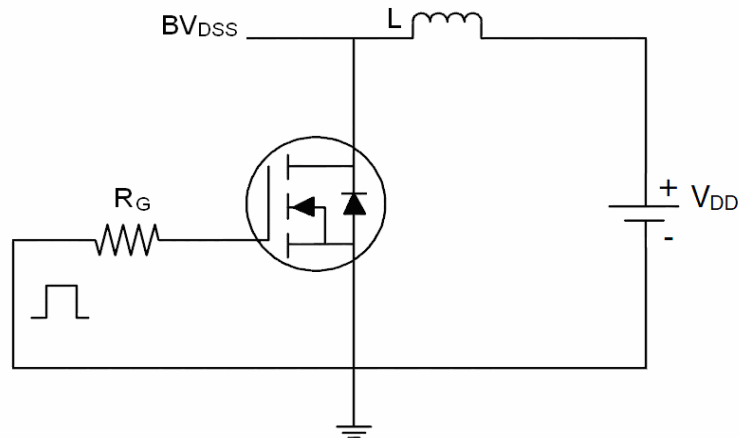
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20	22	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.5	0.7	0.9	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=4A$	-	19	24	m Ω
		$V_{GS}=2.5V, I_D=3A$	-	25	32	
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=4A$	20	-	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	550	-	PF
Output Capacitance	C_{oss}		-	110	-	PF
Reverse Transfer Capacitance	C_{rss}		-	85	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, I_D=4A$ $V_{GEN}=4.5V, R_G=6\Omega$	-	8	-	nS
Turn-on Rise Time	t_r		-	9	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	15	-	nS
Turn-Off Fall Time	t_f		-	4	-	nS
Total Gate Charge	Q_g	$V_{DS}=10V, I_D=4A,$ $V_{GS}=4.5V$	-	6	-	nC
Gate-Source Charge	Q_{gs}		-	1.5	-	nC
Gate-Drain Charge	Q_{gd}		-	1.6	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=4A$	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	4	A

Notes:

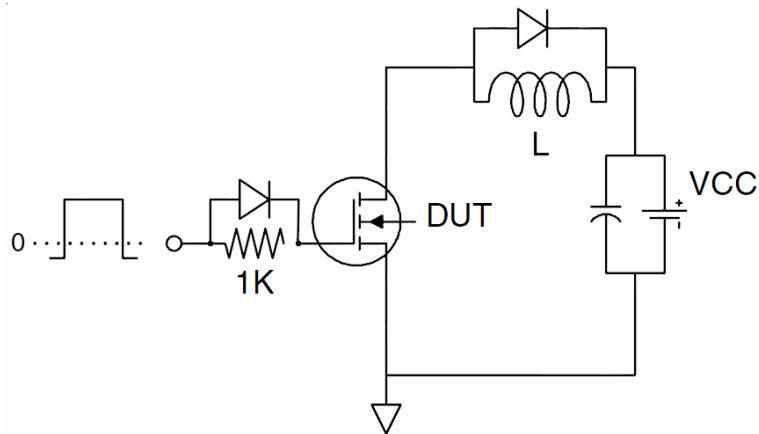
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Test Circuit

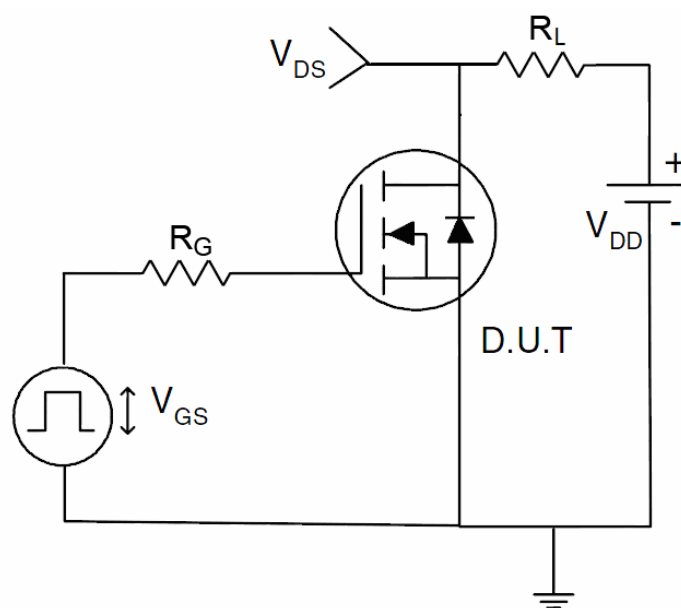
1) E_{AS} Test Circuits



2) Gate Charge Test Circuit:



3) Switch Time Test Circuit:



Typical Electrical and Thermal Characteristics (Curves)

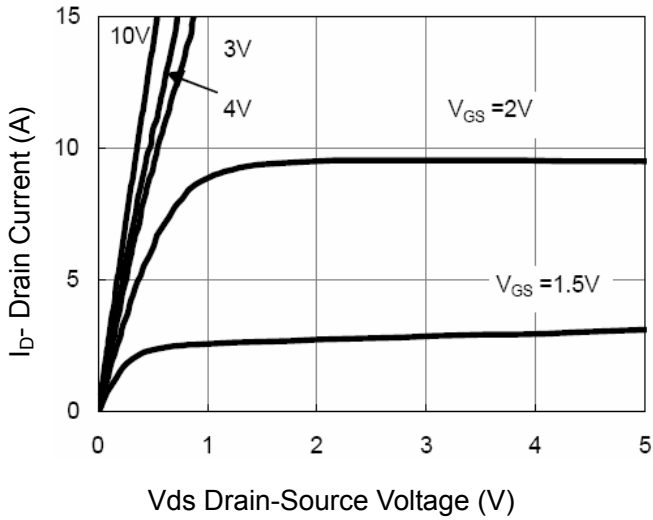


Figure 1 Output Characteristics

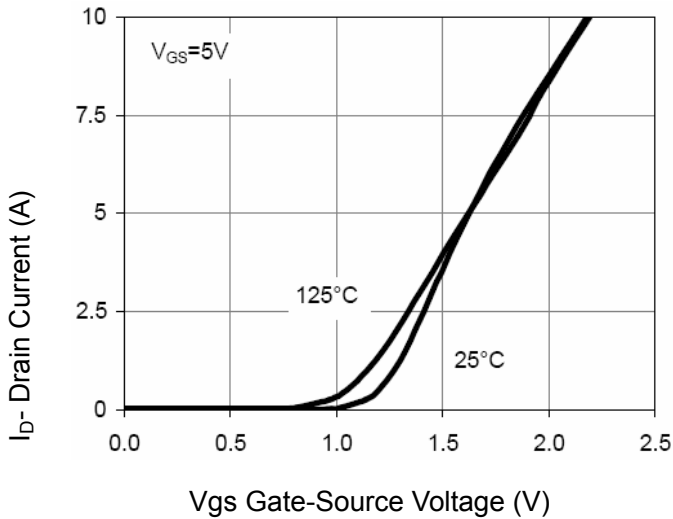


Figure 2 Transfer Characteristics

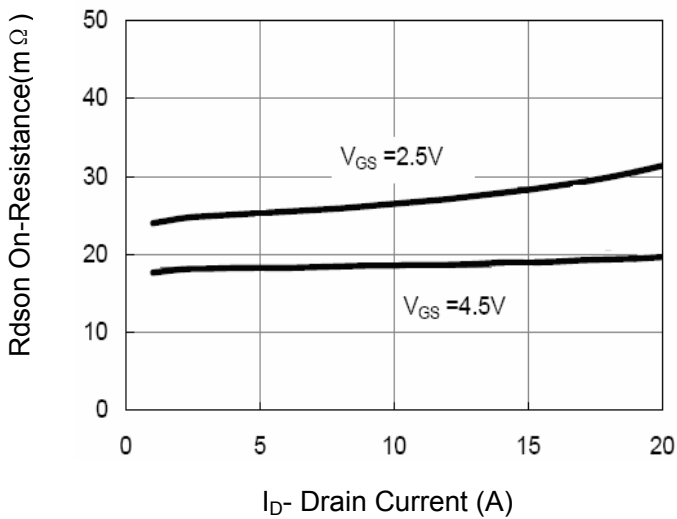


Figure 3 Rdson- Drain Current

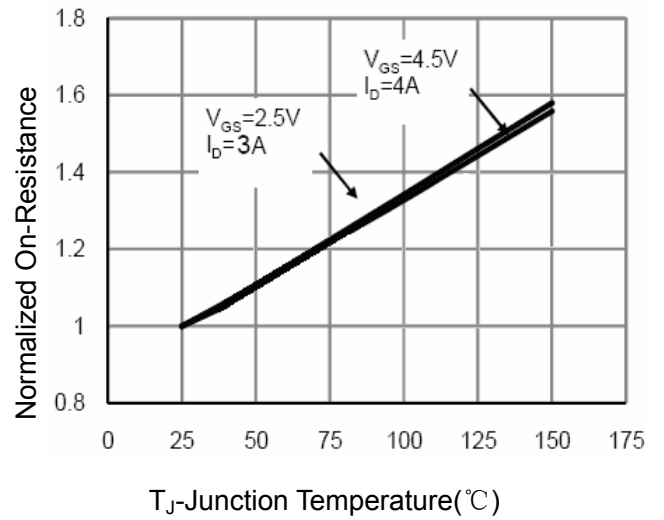


Figure 4 Rdson-Junction Temperature

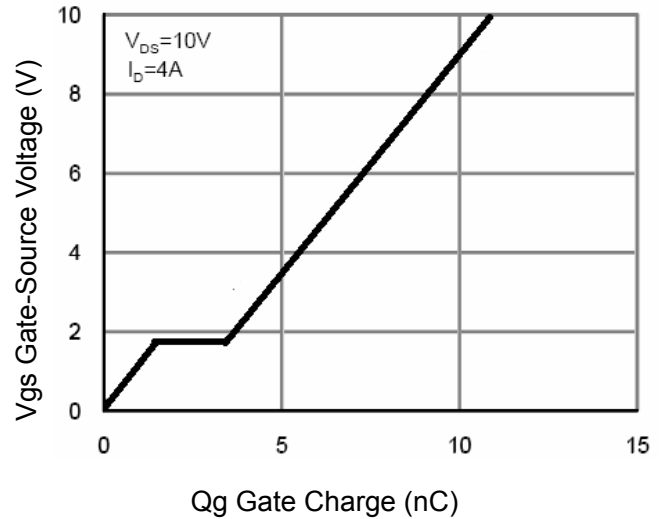


Figure 5 Gate Charge

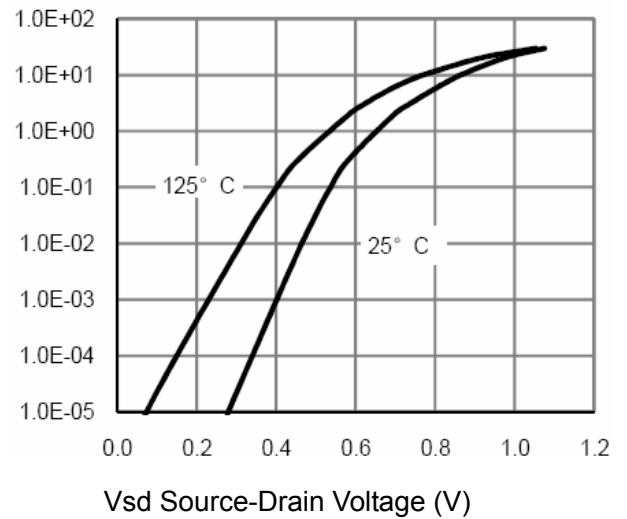


Figure 6 Source- Drain Diode Forward

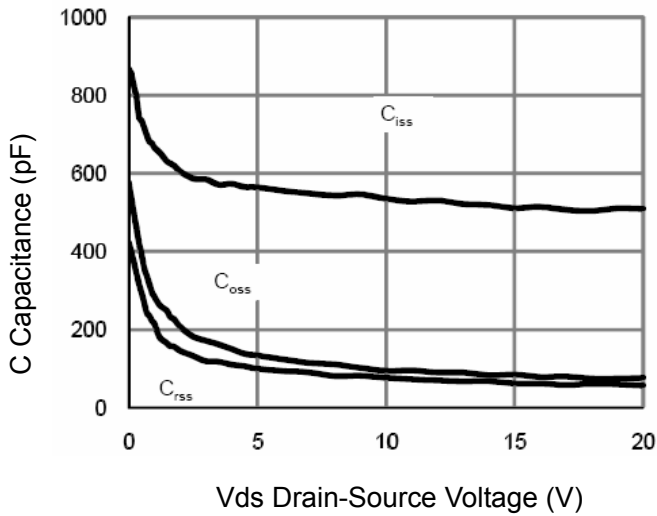


Figure 7 Capacitance vs Vds

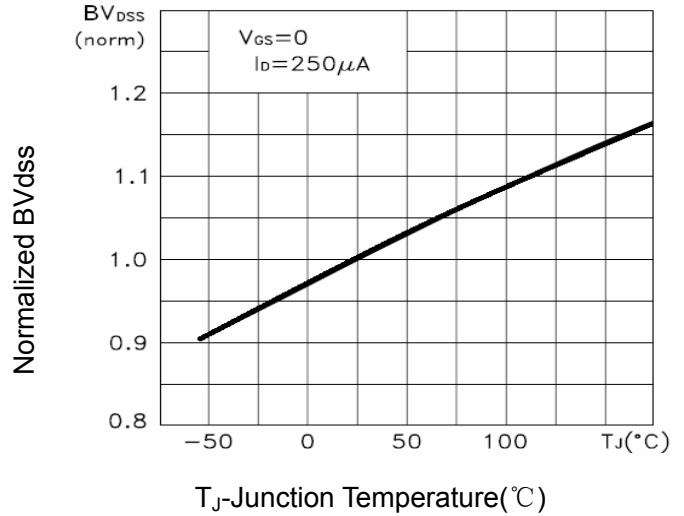


Figure 9 BV_{DSS} vs Junction Temperature

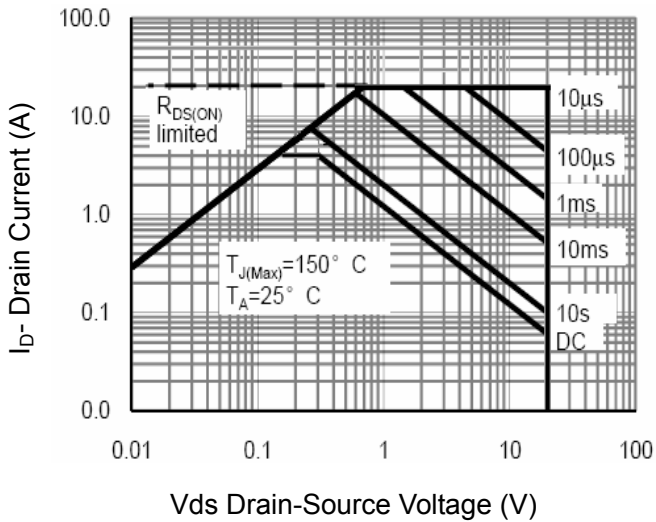


Figure 8 Safe Operation Area

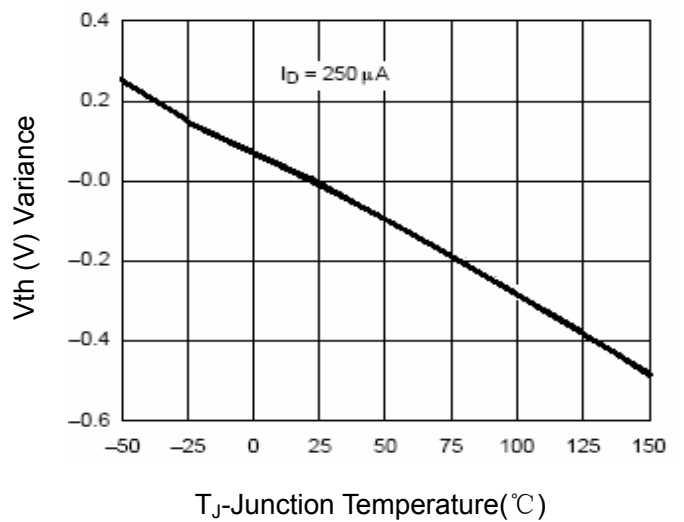


Figure 10 $V_{GS(th)}$ vs Junction Temperature

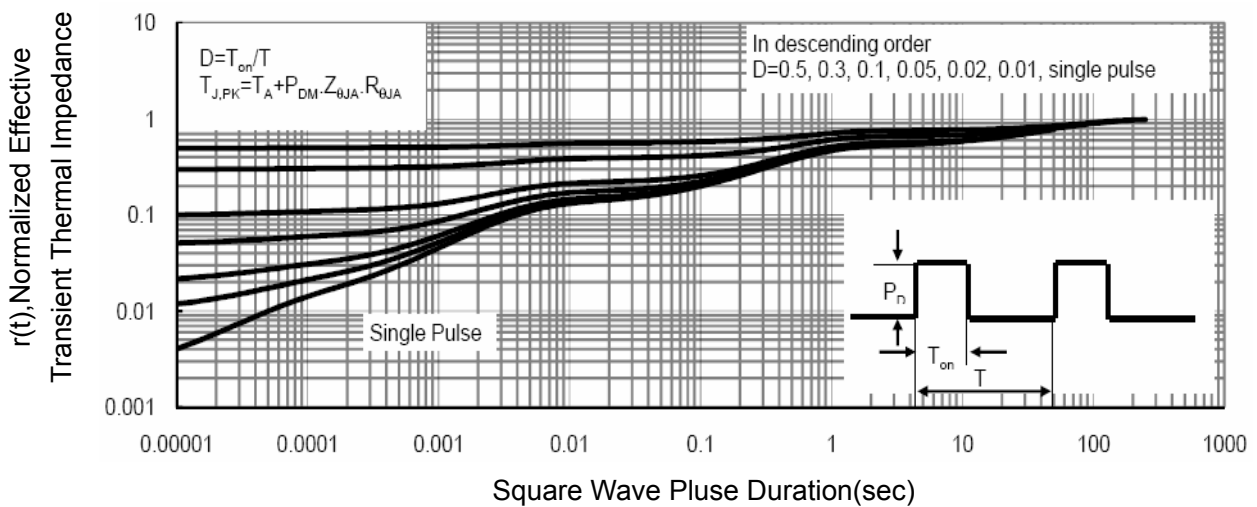
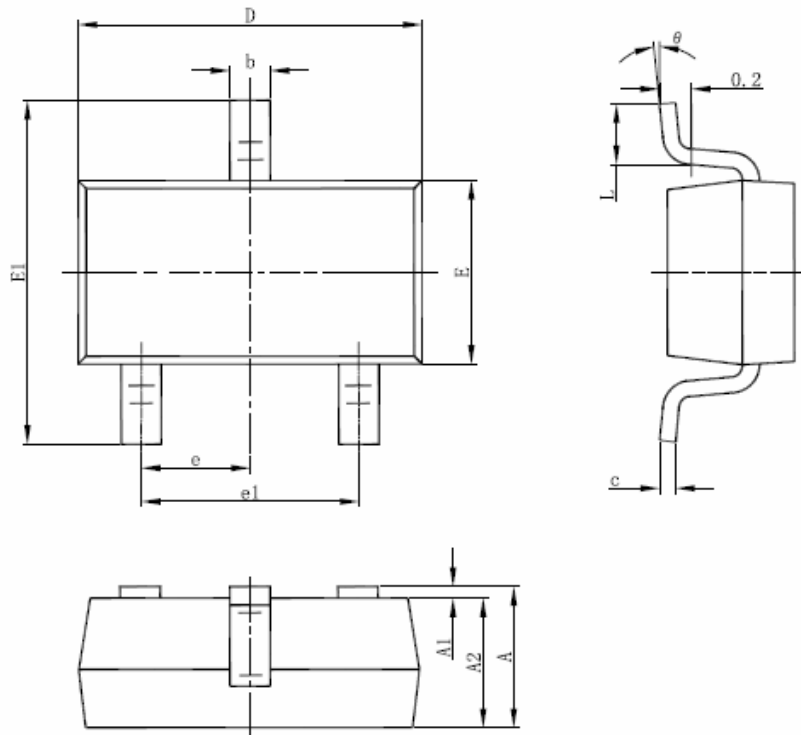


Figure 11 Normalized Maximum Transient Thermal Impedance

SOT-23-3L Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

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